

**31 EDS Members Elected to the IEEE
Grade of Fellow Effective 1 January 2002**

**Vasudev Kalkunte Aatre, Defense R&D Organization, Government of India,
New Delhi, India**

For leadership in research and development for strategic electronics and defense systems

Narain Das Arora, Simplex Solutions, Inc., Sunnyvale, CA, USA

For contributions to the development of MOSFET compact models for circuit simulation

Joachim N. Burghartz, The Netherlands

For contributions to integrated high-speed and radio-frequency silicon devices and components.

Keh-Yung Cheng, University of Illinois at Urbana Champaign, Urbana, IL, USA

For contributions to semiconductor heterostructure materials and devices using molecular beam epitaxy

Bijan Davari, IBM, Hopewell Junction, NY, USA

For contributions to high performance deep-submicron CMOS technology development

Nico De Rooij, University of Neuchatel, Neuchatel, Switzerland

For contributions to microelectrical/mechanical systems and technology transfer to the marketplace

Toshio Goto, Nagoya University, Aichi, Japan

For contributions to plasma processing, gaseous electronics and lasers

James W. Haslett, University of Calgary, Calgary, Canada

For contributions to high temperature instrumentation and noise in solid-state electronics

**Allen Ray Hefner, National Inst. of Standards and Tech., Gaithersburg, MD,
USA**

For contributions to the theory and modeling of power semiconductor devices

Chang-Gyu Hwang, Samsung Electronics Co., Ltd., Yongin, Korea

For contributions to, and leadership in, device and process technologies for high density memories

Chennupati Jagadish, Australian National University, Canberra, Australia For contributions to III-V compound semiconductor optoelectronic device integration

Ralph Boyd James, Brookhaven National Laboratory, Upton, NY, USA

For contributions to and leadership in the development of wide band-gap compound semiconductor devices used for detecting and imaging X- and gamma-ray radiation

Allan Hugh Johnston, Glendale, CA, USA

For contributions to the understanding of space radiation effects in optoelectronics

Rajiv V. Joshi, IBM Research Division, Yorktown Heights, NY, USA

For contributions to chip metallurgy materials and processes, and high performance processor and circuit design

Jack C. Lee, The University of Texas at Austin, Austin, TX, USA

For contributions to the understanding and development of ultra-thin dielectrics and their application to silicon devices

Si-Chen Lee, National Taiwan University, Taipei, Taiwan

For contributions to heterojunction bipolar transistor technology in low noise and high gain applications

Neville Clinton Luhmann, University of California, Davis, CA, USA

For advances in millimeter/submillimeter wave plasma diagnostics, intense microwave plasma interactions, and coherent radiation generation

Leda M. Lunardi, JDS Uniphase Corp., Freehold, NJ, USA

For contributions to the development of high-performance 1.55 um monolithically integrated photoreceiver for optical communication

Akira Matsuzawa, Matsushita Electric Industrial Co., Ltd., Osaka, Japan

For contributions to high-speed A/D converters and mixed-signal integrated circuits

Wolfgang Porod, University of Notre Dame, Notre Dame, IN, USA

For contributions to circuit concepts and architectures for nanoelectronics

Ulrich Lothar Rohde, Synergy Microwave Corp., Paterson, NJ, USA

For contributions to and leadership in the development and industrial implementation of microwave computer-aided design technology

Tadashi Saitoh, Tokyo University of Agriculture & Technology, Tokyo, Japan

For contributions to development of crystalline silicon solar cells and materials for photovoltaic applications

Naoyuki Shigyo, Toshiba Corporation, Semiconductor Company, Yokohama, Japan

For contributions to the development of technology-oriented computer-aided design of semiconductor devices

Rajendra Singh, Clemson University, Clemson, SC, USA

For contributions to and technical leadership in the materials processing and manufacturing of semiconductor devices

Albert J.P. Theuwissen, Philips Semiconductors, Eindhoven, Netherlands

For contributions to the development of CCD image sensors for still photography and HDTV applications

Tseung-Yuen Tseng, National Chiao Tung University, Hsinchu, Taiwan

For contributions to ceramic capacitor and sensor technologies

Toshiaki Tsuchiya, Shimane University, Shimane, Japan

For contributions to the understanding of the reliability physics of MOS devices and the development of hot-carrier-immune CMOS technologies

Charles Wuching Tu, University of California, San Diego, La Jolla, CA, USA

For contributions to molecular beam epitaxy of novel III-V semiconductors

Jan Van der Spiegel, University of Pennsylvania, Philadelphia, PA, USA

For contributions in biologically motivated sensors and information processing systems

Ming C. Wu, University of California, Los Angeles, CA, USA

For contributions to optical micro-electro-mechanical systems and high speed optoelectronics

Toshiaki Yachi, NTT Telecommunication Energy Laboratories, Tokyo, Japan

For contributions to power semiconductor and micro-magnetic devices

**The Nominations of the Following IEEE Members Were Evaluated by EDS
But Are Not Current Members of EDS**

Austin Michael Andrews, II, Alexandria, VA, USA

For technical leadership of government research and development programs

Paul Siu-Chung Ho, The University of Texas at Austin, Austin, TX, USA

For contributions to metalization of and metrology for multilevel interconnects and electronic packaging

Nicholas Reinhardt, Lexington, MA, USA

For contributions to hydrogen thyratrons, high voltage pulse power, high voltage transmission and distribution

Larry F. Weber, Plasmaco, Inc., Highland, NY, USA

For contributions to plasma display technology